

74HC366; 74HCT366

Hex buffer/line driver; 3-state; inverting

Rev. 4 — 4 September 2012

Product data sheet

1. General description

The 74HC366; 74HCT366 is a hex inverter/line driver with 3-state outputs controlled by the output enable inputs ($\overline{OE1}$). A HIGH on $\overline{OE1}$ causes the outputs to assume a high impedance OFF-state. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

The 74HC366; 74HCT366 is functionally identical to:

- 74HC365; 74HCT365, but has inverted outputs

2. Features and benefits

- Inverting outputs
- Input levels:
 - ◆ For 74HC366: CMOS level
 - ◆ For 74HC366: TTL level
- Complies with JEDEC standard no. 7A
- ESD protection:
 - ◆ HBM EIA/JESD22-A114-F exceeds 2000 V
 - ◆ MM EIA/JESD22-A115-A exceeds 200 V
- Specified from -40°C to $+85^{\circ}\text{C}$ and from -40°C to $+125^{\circ}\text{C}$
- Multiple package options



3. Ordering information

Table 1. Ordering information

Type number	Package		Description	Version
	Temperature range	Name		
74HC366				
74HC366D	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HC366N	−40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil); long body	SOT38-1
74HC366PW	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HCT366				
74HCT366D	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT366DB	−40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74HCT366N	−40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil); long body	SOT38-1
74HCT366PW	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1

4. Functional diagram

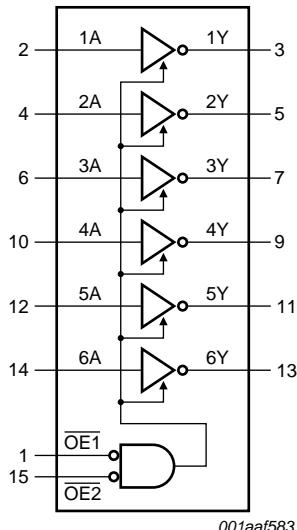


Fig 1. Functional diagram

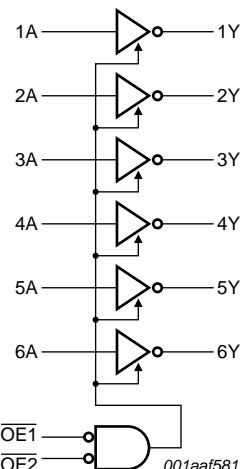


Fig 2. Logic symbol

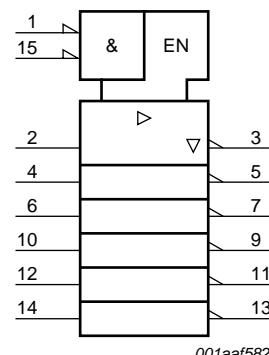


Fig 3. IEC logic symbol

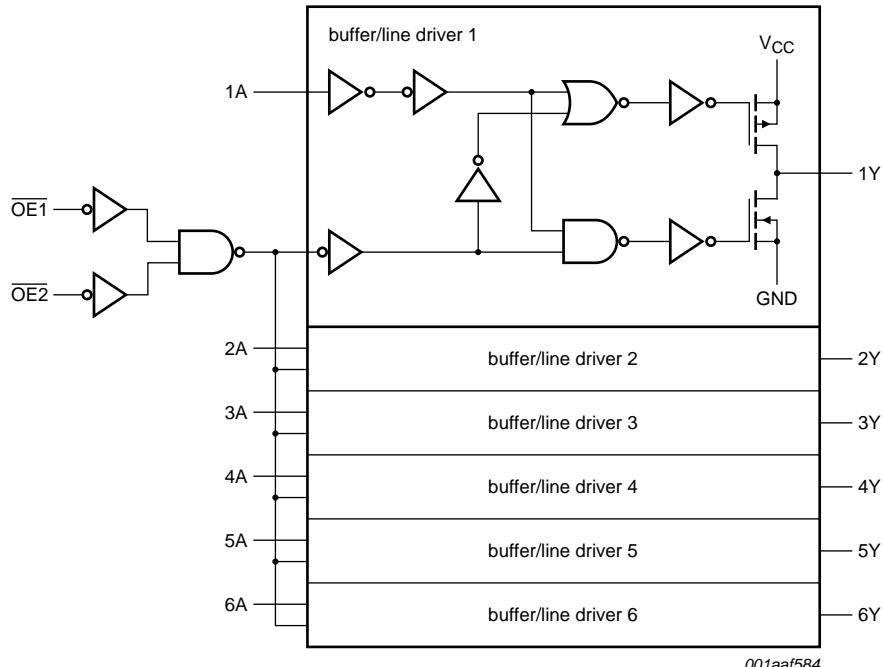


Fig 4. Logic diagram

5. Pinning information

5.1 Pinning

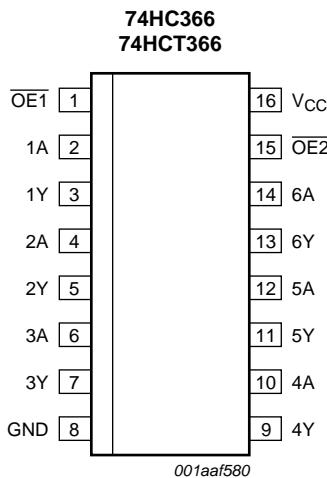


Fig 5. Pin configuration

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
OE1	1	output enable input 1 (active LOW)
1A	2	data input 1
1Y	3	data output 1
2A	4	data input 2
2Y	5	data output 2
3A	6	data input 3
3Y	7	data output 3
GND	8	ground (0 V)
4Y	9	data output 4
4A	10	data input 4
5Y	11	data output 5
5A	12	data input 5
6Y	13	data output 6
6A	14	data input 6
OE2	15	output enable input 2 (active LOW)
V _{CC}	16	supply voltage

6. Functional description

Table 3. Function table^[1]

Control		Input	Output
OE1	OE2	nA	nY
L	L	L	H
L	L	H	L
X	H	X	Z
H	X	X	Z

[1] H = HIGH voltage level;

L = LOW voltage level;

X = don't care;

Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit	
V_{CC}	supply voltage		-0.5	+7	V	
I_{IK}	input clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V	-	± 20	mA	
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	-	± 20	mA	
I_O	output current	$V_O = -0.5$ V to $(V_{CC} + 0.5)$ V	-	± 35	mA	
I_{CC}	supply current		-	70	mA	
I_{GND}	ground current		-	-70	mA	
T_{stg}	storage temperature		-65	+150	°C	
P_{tot}	total power dissipation	DIP16 package	[1]	-	750	mW
		SO16 package	[2]	-	500	mW
		SSOP16 package	[3]	-	500	mW
		TSSOP16 package	[3]	-	500	mW

[1] For DIP16 packages: P_{tot} derates linearly with 12 mW/K above 70 °C.

[2] For SO16 packages: P_{tot} derates linearly with 8 mW/K above 70 °C.

[3] For SSOP16 and TSSOP16 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC366			74HCT366			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0$ V	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5$ V	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0$ V	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics 74HC366

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}	-	-	-	-
		I _O = -20 µA; V _{CC} = 2.0 V	1.9	2.0	-	V
		I _O = -20 µA; V _{CC} = 4.5 V	4.4	4.5	-	V
		I _O = -20 µA; V _{CC} = 6.0 V	5.9	6.0	-	V
		I _O = -6.0 mA; V _{CC} = 4.5 V	3.98	4.32	-	V
		I _O = -7.8 mA; V _{CC} = 6.0 V	5.48	5.81	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}	-	-	-	-
		I _O = 20 µA; V _{CC} = 2.0 V	-	0	0.1	V
		I _O = 20 µA; V _{CC} = 4.5 V	-	0	0.1	V
		I _O = 20 µA; V _{CC} = 6.0 V	-	0	0.1	V
		I _O = 6.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	V
		I _O = 7.8 mA; V _{CC} = 6.0 V	-	0.16	0.26	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	µA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.5	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	8.0	µA
C _I	input capacitance		-	3.5	-	pF
T_{amb} = -40 °C to +85 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	V
		V _{CC} = 4.5 V	3.15	-	-	V
		V _{CC} = 6.0 V	4.2	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	V
		V _{CC} = 4.5 V	-	-	1.35	V
		V _{CC} = 6.0 V	-	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}	-	-	-	-
		I _O = -20 µA; V _{CC} = 2.0 V	1.9	-	-	V
		I _O = -20 µA; V _{CC} = 4.5 V	4.4	-	-	V
		I _O = -20 µA; V _{CC} = 6.0 V	5.9	-	-	V
		I _O = -6.0 mA; V _{CC} = 4.5 V	3.84	-	-	V
		I _O = -7.8 mA; V _{CC} = 6.0 V	5.34	-	-	V

Table 6. Static characteristics 74HC366 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 μ A; V _{CC} = 2.0 V	-	-	0.1	V
		I _O = 20 μ A; V _{CC} = 4.5 V	-	-	0.1	V
		I _O = 20 μ A; V _{CC} = 6.0 V	-	-	0.1	V
		I _O = 6.0 mA; V _{CC} = 4.5 V	-	-	0.33	V
		I _O = 7.8 mA; V _{CC} = 6.0 V	-	-	0.33	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V;	-	-	\pm 1.0	μ A
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 6.0 V	-	-	\pm 5.0	μ A
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	80	μ A
T_{amb} = -40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	V
		V _{CC} = 4.5 V	3.15	-	-	V
		V _{CC} = 6.0 V	4.2	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	V
		V _{CC} = 4.5 V	-	-	1.35	V
		V _{CC} = 6.0 V	-	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 μ A; V _{CC} = 2.0 V	1.9	-	-	V
		I _O = -20 μ A; V _{CC} = 4.5 V	4.4	-	-	V
		I _O = -20 μ A; V _{CC} = 6.0 V	5.9	-	-	V
		I _O = -6.0 mA; V _{CC} = 4.5 V	3.7	-	-	V
		I _O = -7.8 mA; V _{CC} = 6.0 V	5.2	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 μ A; V _{CC} = 2.0 V	-	-	0.1	V
		I _O = 20 μ A; V _{CC} = 4.5 V	-	-	0.1	V
		I _O = 20 μ A; V _{CC} = 6.0 V	-	-	0.1	V
		I _O = 6.0 mA; V _{CC} = 4.5 V	-	-	0.4	V
		I _O = 7.8 mA; V _{CC} = 6.0 V	-	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	\pm 1.0	μ A
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 6.0 V	-	-	\pm 10.0	μ A
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	160	μ A

Table 7. Static characteristics 74HCT366

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = -20 μ A	4.4	4.5	-	V
		I _O = -6.0 mA	3.98	4.32	-	V

Table 7. Static characteristics 74HCT366 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = 20 μ A	-	0	0.1	V
		I _O = 6.0 mA	-	0.16	0.26	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	\pm 0.1	μ A
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND per input pin; other inputs at GND or V _{CC} ; I _O = 0 A; V _{CC} = 5.5 V	-	-	\pm 0.5	μ A
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	8.0	μ A
Δ I _{CC}	additional supply current	V _I = V _{CC} – 2.1 V; other inputs at V _{CC} or GND; I _O = 0 A				
			-	100	360	μ A
			-	100	360	μ A
C _I	input capacitance		-	90	320	μ A
			-	3.5	-	pF
T_{amb} = –40 °C to +85 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = –20 μ A	4.4	-	-	V
		I _O = –6.0 mA	3.84	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
			-	-	0.1	V
			-	-	0.33	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	\pm 1.0	μ A
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND per input pin; other inputs at GND or V _{CC} ; I _O = 0 A; V _{CC} = 5.5 V			\pm 5.0	μ A
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	80	μ A
Δ I _{CC}	additional supply current	V _I = V _{CC} – 2.1 V; other inputs at V _{CC} or GND; I _O = 0 A				
			-	-	450	μ A
			-	-	450	μ A
			-	-	400	μ A
T_{amb} = –40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
			-	-	0.8	V
			4.4	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
			-	-	0.4	V
			-	-	0.7	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	\pm 1.0	μ A
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND per input pin; other inputs at GND or V _{CC} ; I _O = 0 A; V _{CC} = 5.5 V	-	-	\pm 10.0	μ A

Table 7. Static characteristics 74HCT366 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	160	μ A
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 2.1$ V; other inputs at V_{CC} or GND; $I_O = 0$ A	-	-	490	μ A
		pins nA	-	-	490	μ A
		pin $\overline{OE1}$	-	-	490	μ A
		pin $\overline{OE2}$	-	-	441	μ A

10. Dynamic characteristics

Table 8. Dynamic characteristics 74HC366Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; see test circuit [Figure 8](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{amb} = 25$ °C						
t_{pd}	propagation delay	nA to nY; see Figure 6		[1]		
		$V_{CC} = 2.0$ V	-	33	100	ns
		$V_{CC} = 4.5$ V	-	12	20	ns
		$V_{CC} = 5$ V; $C_L = 15$ pF	-	10	-	ns
		$V_{CC} = 6.0$ V	-	10	17	ns
t_{en}	enable time	\overline{OE} to nY; see Figure 7		[2]		
		$V_{CC} = 2.0$ V	-	44	150	ns
		$V_{CC} = 4.5$ V	-	16	30	ns
		$V_{CC} = 6.0$ V	-	13	26	ns
t_{dis}	disable time	\overline{OE} to nY; see Figure 7		[3]		
		$V_{CC} = 2.0$ V	-	55	150	ns
		$V_{CC} = 4.5$ V	-	20	30	ns
		$V_{CC} = 6.0$ V	-	16	26	ns
t_t	transition time	see Figure 6		[4]		
		$V_{CC} = 2.0$ V	-	14	60	ns
		$V_{CC} = 4.5$ V	-	5	12	ns
		$V_{CC} = 6.0$ V	-	4	10	ns
C_{PD}	power dissipation capacitance	per buffer; $V_I = \text{GND}$ to V_{CC}		[5]	-	pF
$T_{amb} = -40$ °C to +85 °C						
t_{pd}	propagation delay	nA to nY; see Figure 6		[1]		
		$V_{CC} = 2.0$ V	-	-	125	ns
		$V_{CC} = 4.5$ V	-	-	25	ns
		$V_{CC} = 6.0$ V	-	-	21	ns
t_{en}	enable time	\overline{OE} to nY; see Figure 7		[2]		
		$V_{CC} = 2.0$ V	-	-	190	ns
		$V_{CC} = 4.5$ V	-	-	38	ns
		$V_{CC} = 6.0$ V	-	-	33	ns

Table 8. Dynamic characteristics 74HC366 ...continuedVoltages are referenced to GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; see test circuit [Figure 8](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{dis}	disable time	$\overline{OE_n}$ to nY ; see Figure 7	[3]			
		$V_{CC} = 2.0 \text{ V}$	-	-	190	ns
		$V_{CC} = 4.5 \text{ V}$	-	-	38	ns
		$V_{CC} = 6.0 \text{ V}$	-	-	33	ns
t_t	transition time	see Figure 6	[4]			
		$V_{CC} = 2.0 \text{ V}$	-	-	75	ns
		$V_{CC} = 4.5 \text{ V}$	-	-	15	ns
		$V_{CC} = 6.0 \text{ V}$	-	-	13	ns
$T_{amb} = -40 \text{ }^{\circ}\text{C to } +125 \text{ }^{\circ}\text{C}$						
t_{pd}	propagation delay	nA to nY ; see Figure 6	[1]			
		$V_{CC} = 2.0 \text{ V}$	-	-	150	ns
		$V_{CC} = 4.5 \text{ V}$	-	-	30	ns
		$V_{CC} = 6.0 \text{ V}$	-	-	26	ns
t_{en}	enable time	$\overline{OE_n}$ to nY ; see Figure 7	[2]			
		$V_{CC} = 2.0 \text{ V}$	-	-	225	ns
		$V_{CC} = 4.5 \text{ V}$	-	-	45	ns
		$V_{CC} = 6.0 \text{ V}$	-	-	38	ns
t_{dis}	disable time	$\overline{OE_n}$ to nY ; see Figure 7	[3]			
		$V_{CC} = 2.0 \text{ V}$	-	-	225	ns
		$V_{CC} = 4.5 \text{ V}$	-	-	45	ns
		$V_{CC} = 6.0 \text{ V}$	-	-	38	ns
t_t	transition time	see Figure 6	[4]			
		$V_{CC} = 2.0 \text{ V}$	-	-	90	ns
		$V_{CC} = 4.5 \text{ V}$	-	-	18	ns
		$V_{CC} = 6.0 \text{ V}$	-	-	15	ns

[1] t_{pd} is the same as t_{PHL} and t_{PLH} .[2] t_{en} is the same as t_{PZH} and t_{PZL} .[3] t_{dis} is the same as t_{PHZ} and t_{PLZ} .[4] t_t is the same as t_{THL} and t_{TLH} .[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

 f_i = input frequency in MHz; f_o = output frequency in MHz; C_L = output load capacitance in pF; V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\sum(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

Table 9. Dynamic characteristics 74HCT366Voltages are referenced to GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; see test circuit [Figure 8](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$T_{amb} = 25^\circ\text{C}$							
t_{pd}	propagation delay	nA to nY; see Figure 6	[1]				
		$V_{CC} = 4.5 \text{ V}$	-	13	24	ns	
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	11	-	ns	
t_{en}	enable time	\overline{OEn} to nY; $V_{CC} = 4.5 \text{ V}$; see Figure 7	[2]	-	16	35	ns
t_{dis}	disable time	\overline{OEn} to nY; $V_{CC} = 4.5 \text{ V}$; see Figure 7	[3]	-	20	35	ns
t_t	transition time	$V_{CC} = 4.5 \text{ V}$; see Figure 6	[4]	-	5	12	ns
C_{PD}	power dissipation capacitance	per buffer; $V_I = \text{GND}$ to $(V_{CC} - 1.5 \text{ V})$	[5]	-	30	-	pF
$T_{amb} = -40^\circ\text{C to } +85^\circ\text{C}$							
t_{pd}	propagation delay	nA to nY; $V_{CC} = 4.5 \text{ V}$; see Figure 6	[1]	-	-	30	ns
t_{en}	enable time	\overline{OEn} to nY; $V_{CC} = 4.5 \text{ V}$; see Figure 7	[2]	-	-	44	ns
t_{dis}	disable time	\overline{OEn} to nY; $V_{CC} = 4.5 \text{ V}$; see Figure 7	[3]	-	-	44	ns
t_t	transition time	$V_{CC} = 4.5 \text{ V}$; see Figure 6	[4]	-	-	15	ns
$T_{amb} = -40^\circ\text{C to } +125^\circ\text{C}$							
t_{pd}	propagation delay	nA to nY; $V_{CC} = 4.5 \text{ V}$; see Figure 6	[1]	-	-	36	ns
t_{en}	enable time	\overline{OEn} to nY; $V_{CC} = 4.5 \text{ V}$; see Figure 7	[2]	-	-	53	ns
t_{dis}	disable time	\overline{OEn} to nY; $V_{CC} = 4.5 \text{ V}$; see Figure 7	[3]	-	-	53	ns
t_t	transition time	$V_{CC} = 4.5 \text{ V}$; see Figure 6	[4]	-	-	18	ns

[1] t_{pd} is the same as t_{PHL} and t_{PLH} .[2] t_{en} is the same as t_{PZH} and t_{PZL} .[3] t_{dis} is the same as t_{PHZ} and t_{PLZ} .[4] t_t is the same as t_{THL} and t_{TLH} .[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

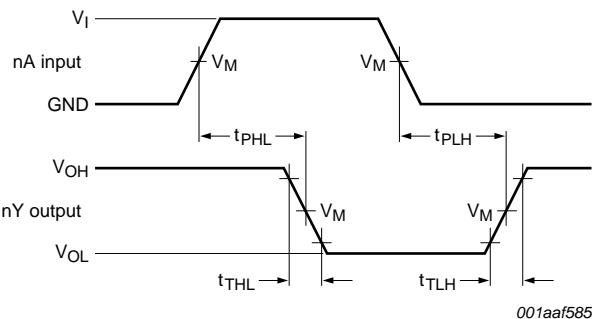
$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

 f_i = input frequency in MHz; f_o = output frequency in MHz; C_L = output load capacitance in pF; V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\sum(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

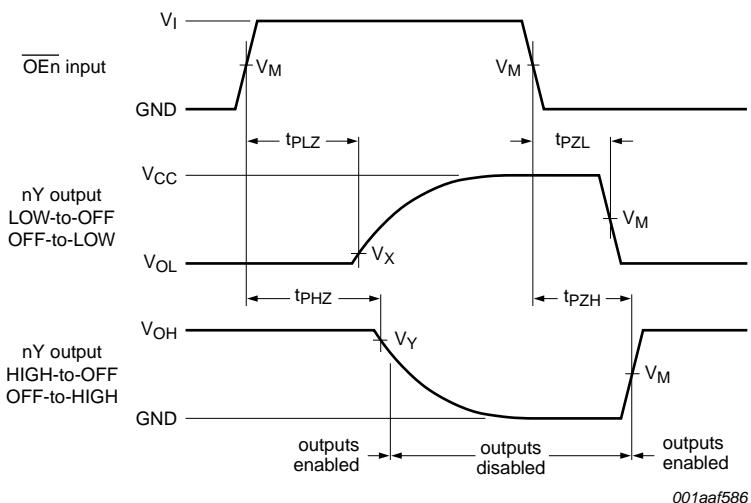
11. Waveforms



Measurement points are given in [Table 10](#).

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 6. Propagation delay data input (nA) to output (nY) and output transition time



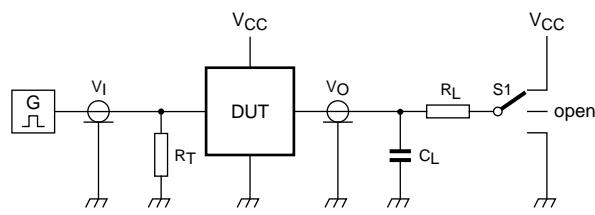
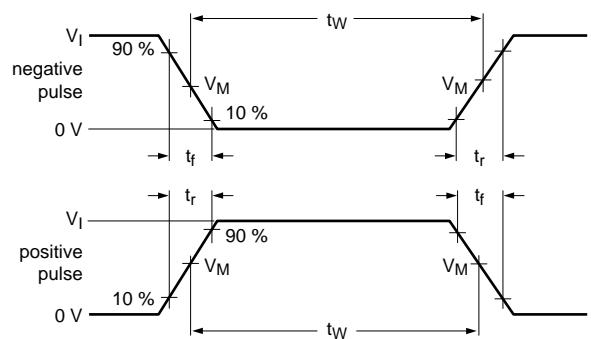
Measurement points are given in [Table 10](#).

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 7. 3-state enable and disable times

Table 10. Measurement points

Type	Input	Output		
		V_M	V_M	V_X
74HC366	$0.5V_{CC}$	$0.5V_{CC}$	$0.1 \times V_{CC}$	$0.9 \times V_{CC}$
74HCT366	1.3 V	1.3 V	$0.1 \times V_{CC}$	$0.9 \times V_{CC}$



001aad983

Test data is given in [Table 11](#).

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator

C_L = Load capacitance including jig and probe capacitance

R_L = Load resistor

$S1$ = Test selection switch

Fig 8. Load circuitry for measuring switching times

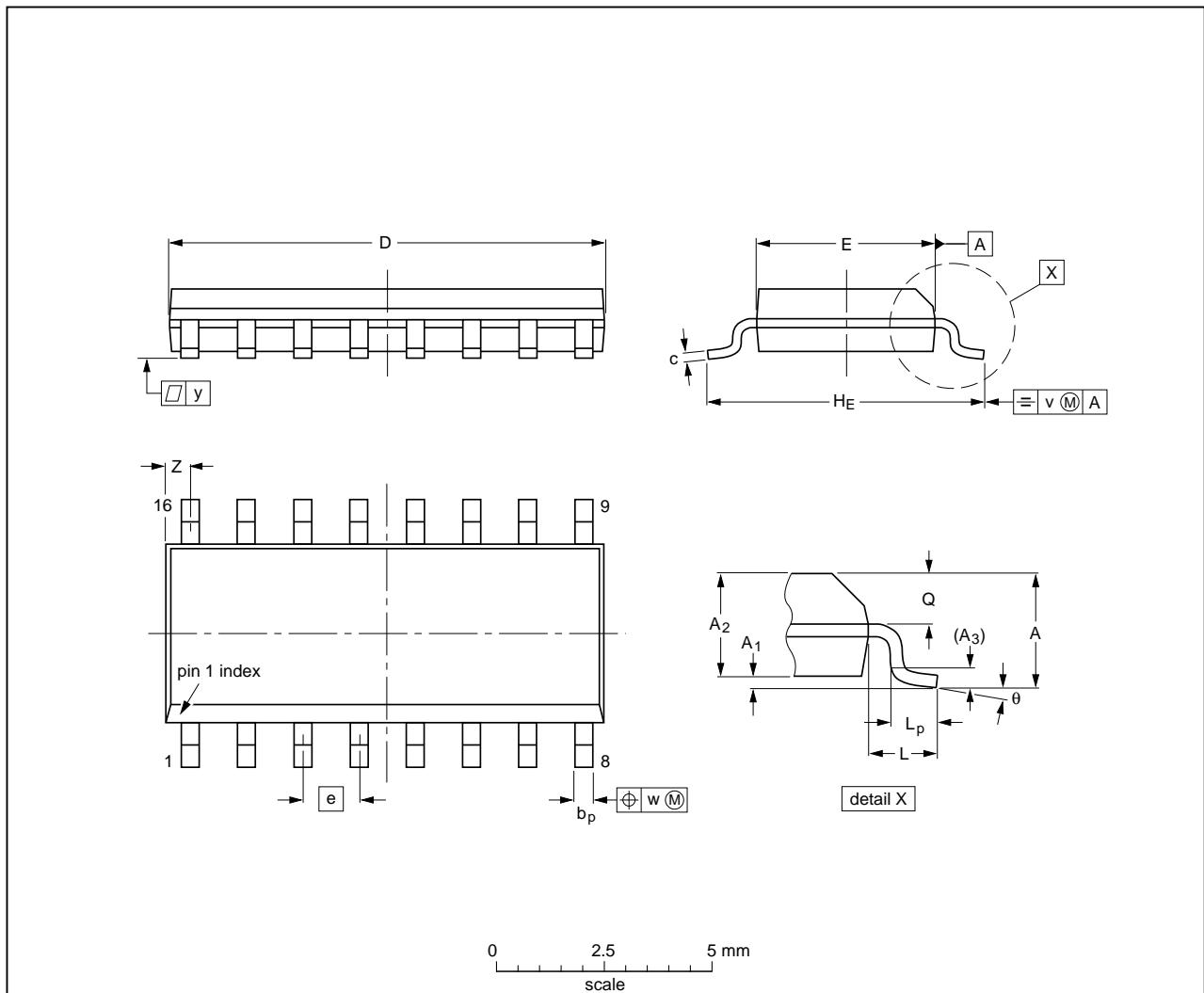
Table 11. Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74HC366	V_{CC}	6 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}
74HCT366	3 V	6 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}

12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	H _E	L	L _p	Q	v	w	y	Z ⁽¹⁾	θ
mm	1.75 0.10	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069 0.004	0.010 0.049	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	0°

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT109-1	076E07	MS-012				99-12-27 03-02-19

Fig 9. Package outline SOT109-1 (SO16)

SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1

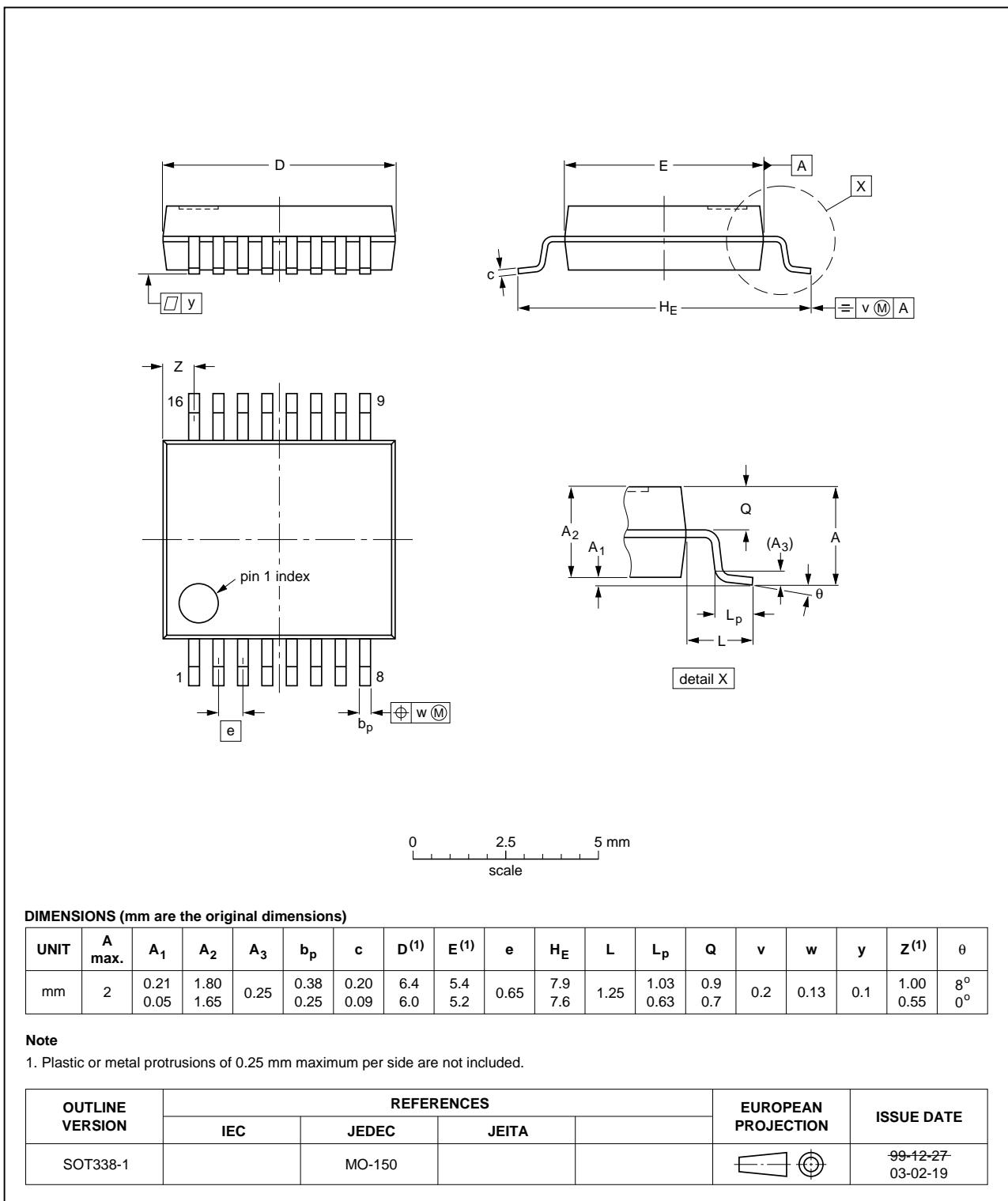
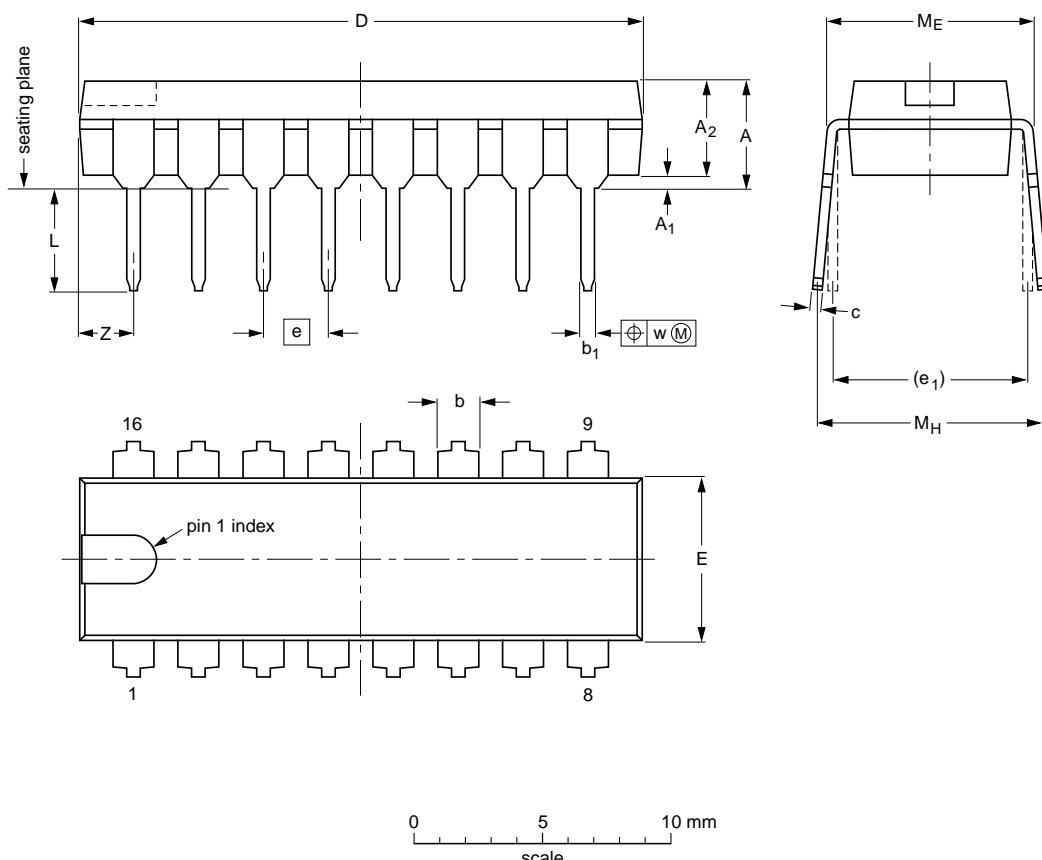


Fig 10. Package outline SOT338-1 (SSOP16)

DIP16: plastic dual in-line package; 16 leads (300 mil); long body

SOT38-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	c	D ⁽¹⁾	E ⁽¹⁾	e	e ₁	L	M _E	M _H	w	Z ⁽¹⁾ max.
mm	4.7	0.51	3.7	1.40 1.14	0.53 0.38	0.32 0.23	21.8 21.4	6.48 6.20	2.54	7.62	3.9 3.4	8.25 7.80	9.5 8.3	0.254	2.2
inches	0.19	0.02	0.15	0.055 0.045	0.021 0.015	0.013 0.009	0.86 0.84	0.26 0.24	0.1	0.3	0.15 0.13	0.32 0.31	0.37 0.33	0.01	0.087

Note

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT38-1	050G09	MO-001	SC-503-16			99-12-27 03-02-13

Fig 11. Package outline SOT38-1 (DIP16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

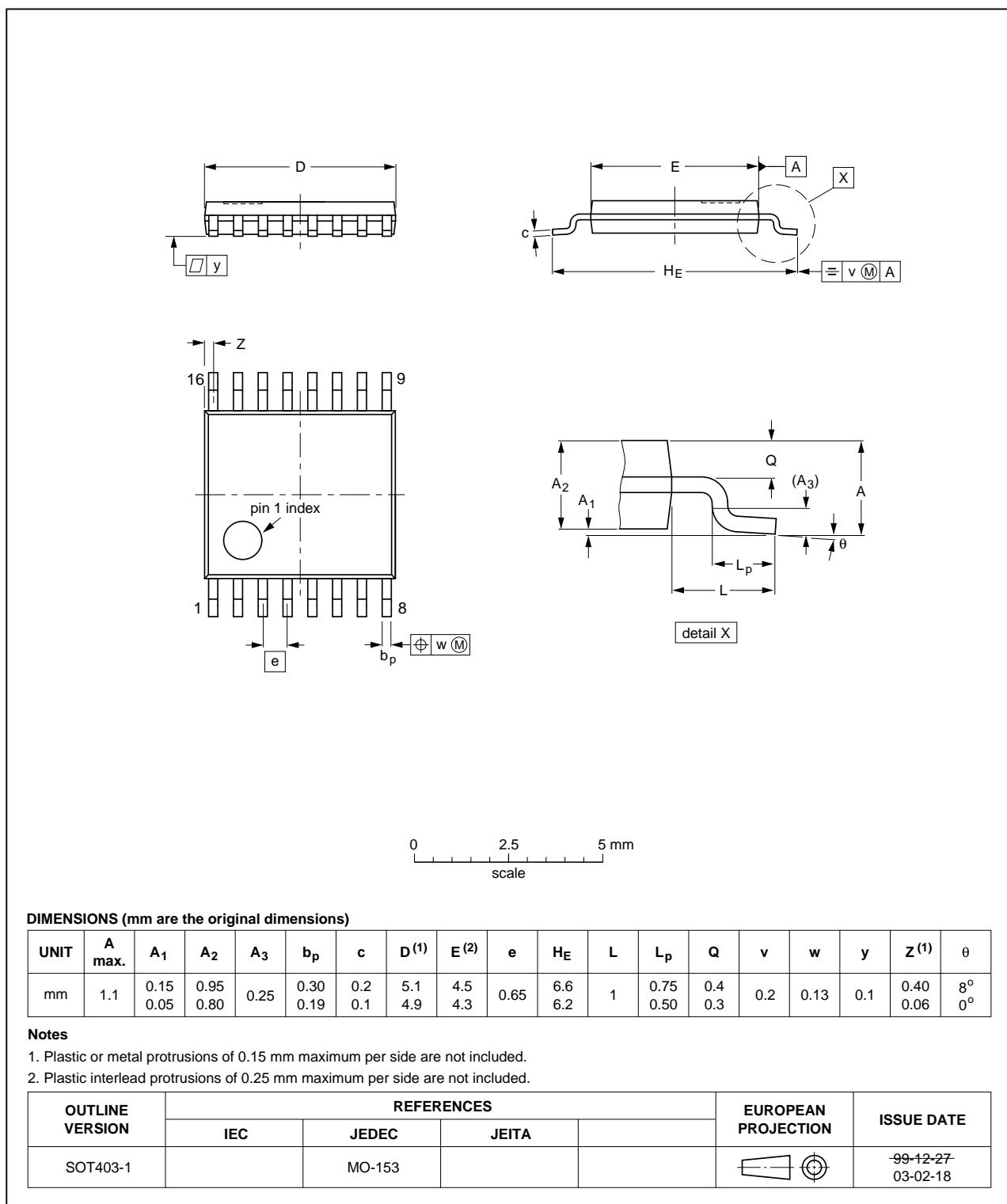


Fig 12. Package outline SOT403-1 (TSSOP16)

13. Abbreviations

Table 12. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model

14. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT366 v.4	20120904	Product data sheet	-	74HC_HCT366 v.3
Modifications:	• Legal pages updated.			
74HC_HCT366 v.3	20061121	Product data sheet	-	74HC_HCT366_CNV v.2
74HC_HCT366_CNV v.2	19901201	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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17. Contents

1	General description	1
2	Features and benefits	1
3	Ordering information	2
4	Functional diagram	2
5	Pinning information	3
5.1	Pinning	3
5.2	Pin description	4
6	Functional description	4
7	Limiting values	5
8	Recommended operating conditions	5
9	Static characteristics	6
10	Dynamic characteristics	9
11	Waveforms	12
12	Package outline	14
13	Abbreviations	18
14	Revision history	18
15	Legal information	19
15.1	Data sheet status	19
15.2	Definitions.....	19
15.3	Disclaimers.....	19
15.4	Trademarks.....	20
16	Contact information	20
17	Contents	21

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